

HD74HC563/HD74HC573

Octal Transparent Latches (with 3-state outputs)

HITACHI

Description

When the latch enable (LE) input is high, the Q outputs of HD74HC563 will follow the inversion of the D inputs and the Q outputs of HD74HC573 will follow the D inputs. When the latch enable goes low, data at the D inputs will be retained at the outputs until latch enable returns high again. When a high logic level is applied to the output control input, all outputs go to a high impedance state, regardless of what signals are present at the other inputs and the state of the storage elements.

Features

- High Speed Operation: t_{pd} (Data to Q, \overline{Q}) = 11 ns typ ($C_L = 50$ pF)
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 2$ to 6 V
- Low Input Current: 1 μ A max
- Low Quiescent Supply Current: I_{CC} (static) = 4 μ A max ($T_a = 25^\circ\text{C}$)

Function Table

Output Control	Latch Enable	Data	Outputs	
			HD74HC563	HD74HD573
L	H	H	L	H
L	H	L	H	L
L	L	X	$\overline{Q_0}$	Q_0
H	X	X	Z	Z

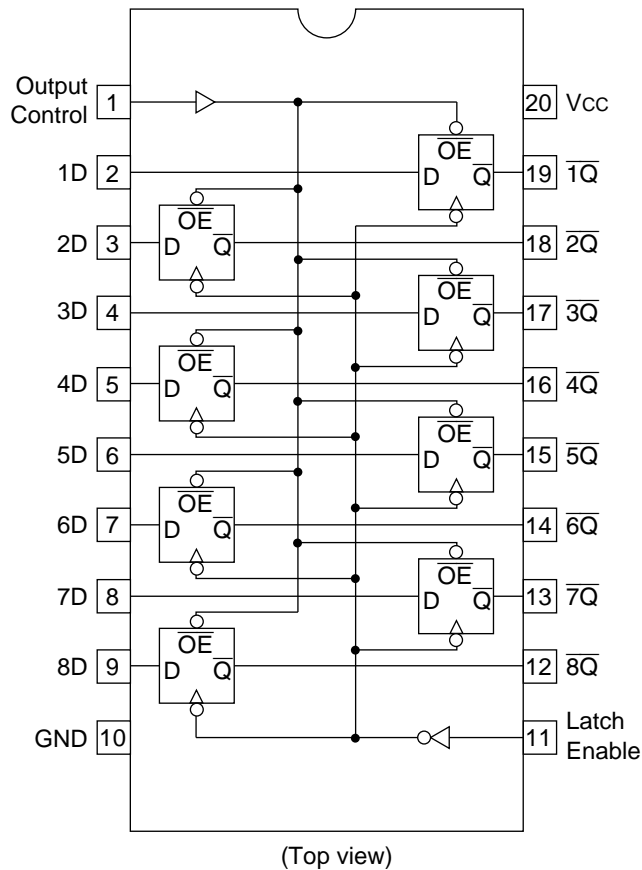
Q_0 : level of Q before the indicated Steady-state input conditions were established.

$\overline{Q_0}$: complement of Q_0 or level of \overline{Q} before the indicated Steady-state input conditions were established.

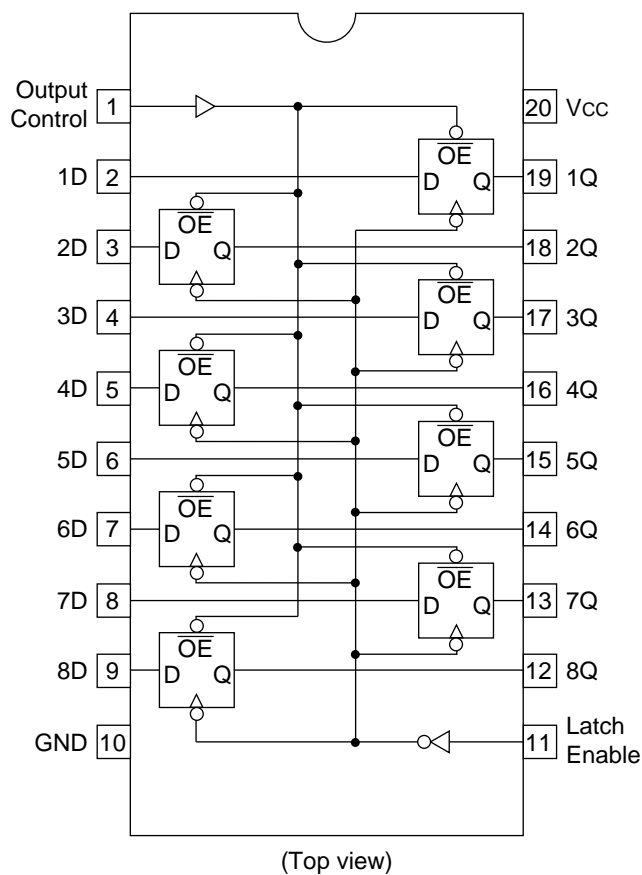
HD74HC563/HD74HC573

Pin Arrangement

HD74HC563



HD74HC573

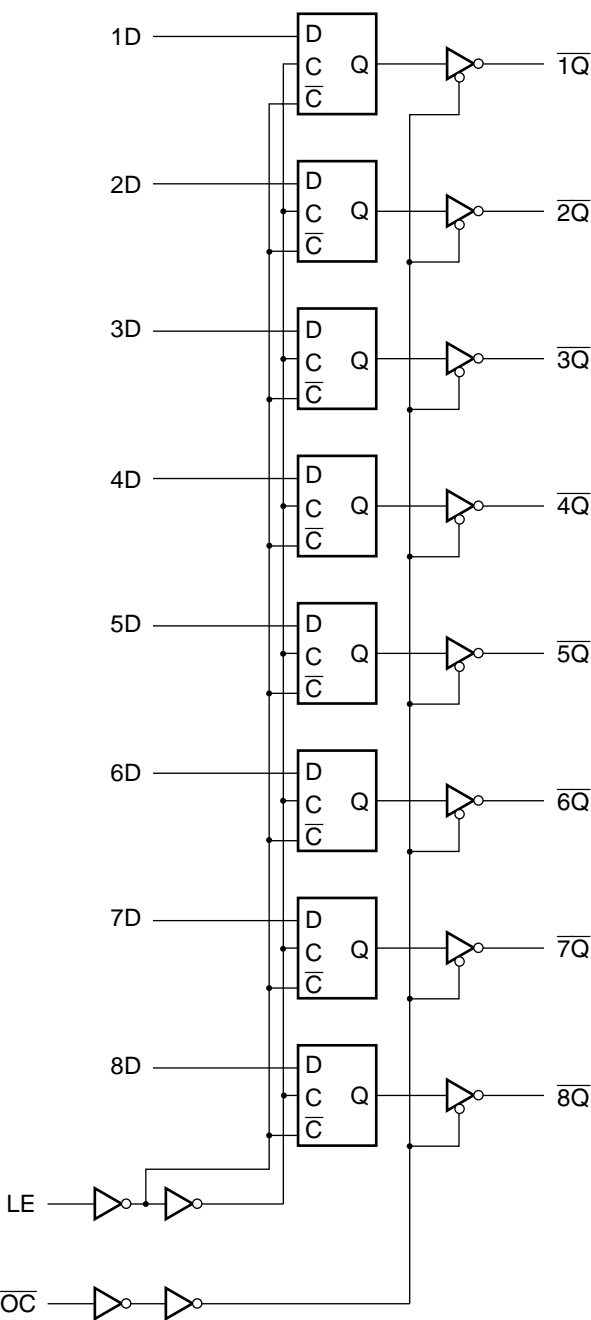


Absolute Maximum Ratings

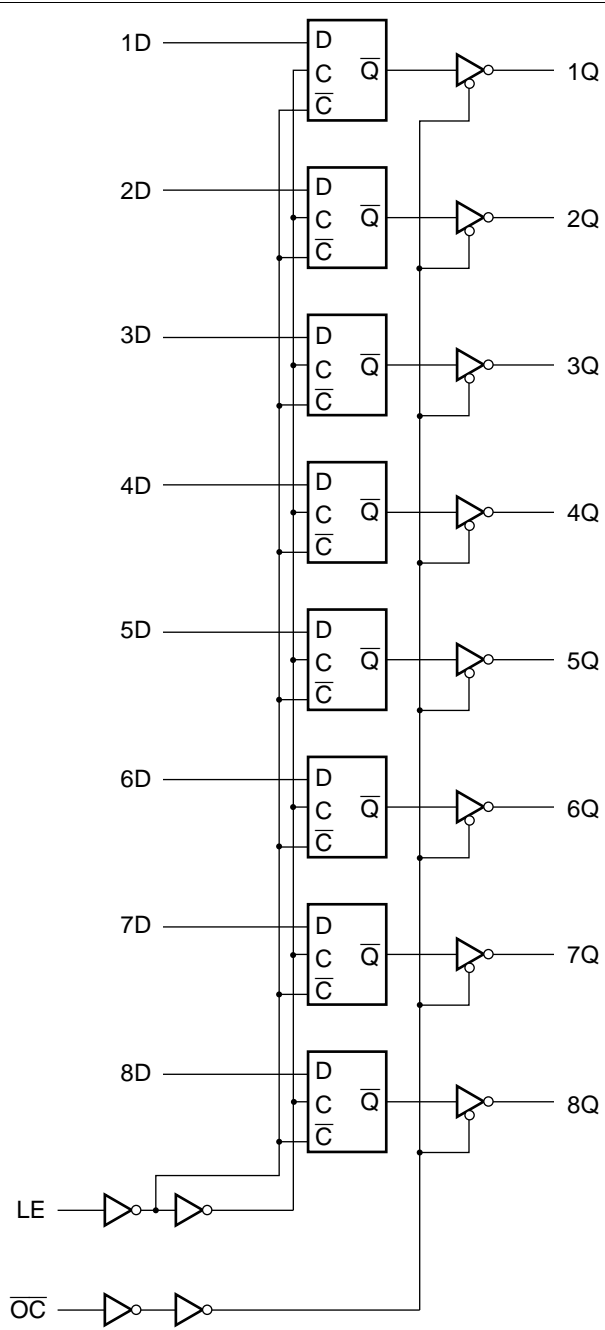
Item	Symbol	Rating	Unit
Supply voltage range	V_{CC}	-0.5 to +7.0	V
Input voltage	V_{IN}	-0.5 to $V_{CC} + 0.5$	V
Output voltage	V_{OUT}	-0.5 to $V_{CC} + 0.5$	V
Output current	I_{OUT}	± 35	mA
DC current drain per V_{CC} , GND	I_{CC} , I_{GND}	± 75	mA
DC input diode current	I_{IK}	± 20	mA
DC output diode current	I_{OK}	± 20	mA
Power Dissipation per package	P_T	500	mW
Storage temperature	Tstg	-65 to +150	°C

Block Diagram

HD74HC563



HD74HC573

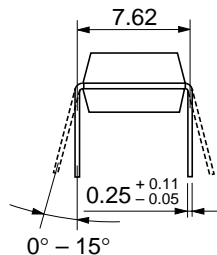
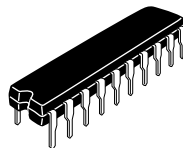
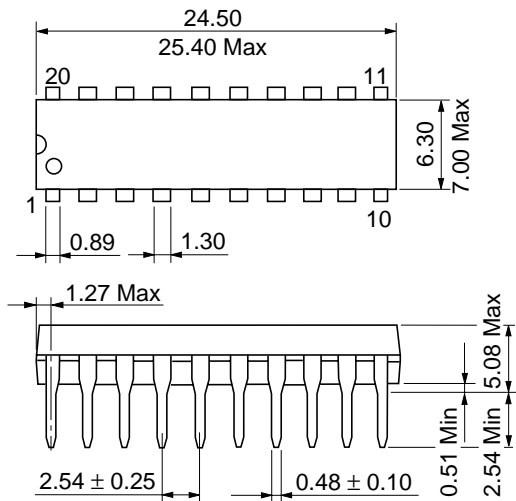


DC Characteristics

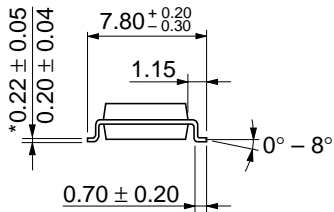
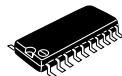
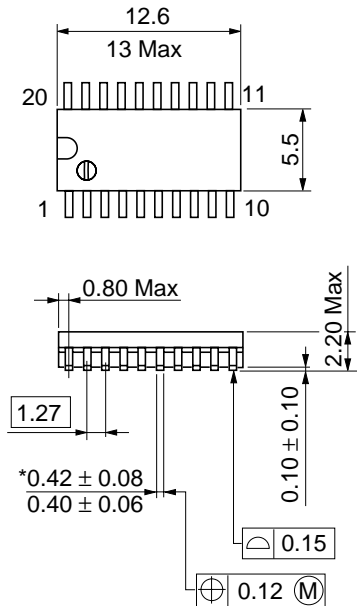
Item	Symbol	V _{CC} (V)	Ta = 25°C			Ta = -40 to +85°C		Unit	Test Conditions	
			Min	Typ	Max	Min	Max			
Input voltage	V _{IH}	2.0	1.5	—	—	1.5	—	V		
		4.5	3.15	—	—	3.15	—			
		6.0	4.2	—	—	4.2	—			
	V _{IL}	2.0	—	—	0.5	—	0.5	V		
		4.5	—	—	1.35	—	1.35			
		6.0	—	—	1.8	—	1.8			
Output voltage	V _{OH}	2.0	1.9	2.0	—	1.9	—	V	Vin = V _{IH} or V _{IL} I _{OH} = -20 μA	
		4.5	4.4	4.5	—	4.4	—			
		6.0	5.9	6.0	—	5.9	—			
		4.5	4.18	—	—	4.13	—			I _{OH} = -6 mA
		6.0	5.68	—	—	5.63	—			I _{OH} = -7.8 mA
	V _{OL}	2.0	—	0.0	0.1	—	0.1	V	Vin = V _{IH} or V _{IL} I _{OL} = 20 μA	
		4.5	—	0.0	0.1	—	0.1			
		6.0	—	0.0	0.1	—	0.1			
		4.5	—	—	0.26	—	0.33			I _{OL} = 6 mA
		6.0	—	—	0.26	—	0.33			I _{OL} = 7.8 mA
Off-state output current	I _{OZ}	6.0	—	—	±0.5	—	±5.0	μA	Vin = V _{IH} or V _{IL} , Vout = V _{CC} or GND	
Input current	I _{in}	6.0	—	—	±0.1	—	±1.0	μA	Vin = V _{CC} or GND	
Quiescent supply current	I _{CC}	6.0	—	—	4.0	—	40	μA	Vin = V _{CC} or GND, Iout = 0 μA	

AC Characteristics (C_L = 50 pF, Input t_r = t_f = 6 ns)

Item	Symbol	V _{CC} (V)	Ta = 25°C			Ta = -40 to +85°C		Unit	Test Conditions
			Min	Typ	Max	Min	Max		
Propagation delay time	t _{PLH}	2.0	—	—	110	—	140	ns	Data to \overline{Q}
	t _{PHL}	4.5	—	11	22	—	28		
		6.0	—	—	19	—	24		
	t _{PLH}	2.0	—	—	115	—	145	ns	Clock to \overline{Q}
	t _{PHL}	4.5	—	13	23	—	29		
		6.0	—	—	20	—	25		
Output enable time	t _{ZH}	2.0	—	—	150	—	190	ns	
	t _{ZL}	4.5	—	14	30	—	38		
		6.0	—	—	26	—	33		
Output disable time	t _{HZ}	2.0	—	—	150	—	190	ns	
	t _{LZ}	4.5	—	15	30	—	38		
		6.0	—	—	26	—	33		
Setup time	t _{su}	2.0	75	—	—	90	—	ns	
		4.5	15	2	—	19	—		
		6.0	13	—	—	16	—		
Hold time	t _h	2.0	5	—	—	5	—	ns	
		4.5	5	-1	—	5	—		
		6.0	5	—	—	5	—		
Pulse width	t _w	2.0	80	—	—	100	—	ns	
		4.5	16	4	—	20	—		
		6.0	14	—	—	17	—		
Output rise/fall time	t _{TLH}	2.0	—	—	60	—	75	ns	
	t _{THL}	4.5	—	4	12	—	15		
		6.0	—	—	10	—	13		
Input capacitance	C _{in}	—	—	5	10	—	10	pF	

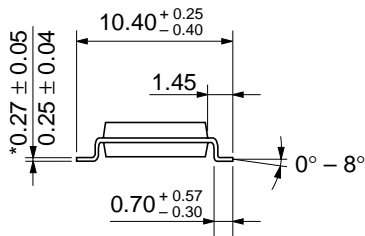
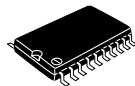
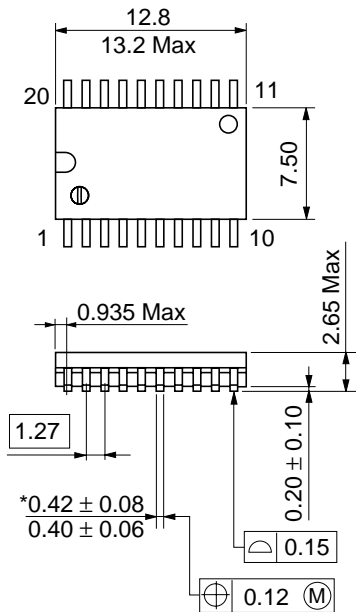


Hitachi Code	DP-20N
JEDEC	—
EIAJ	Conforms
Weight (reference value)	1.26 g



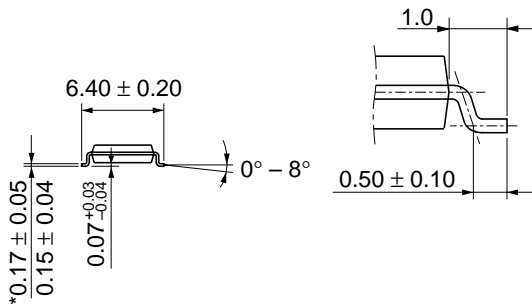
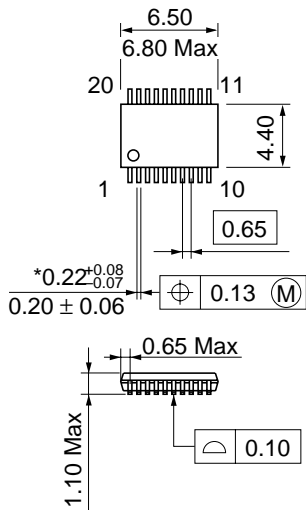
*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DA
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.31 g



*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DB
JEDEC	Conforms
EIAJ	—
Weight (reference value)	0.52 g



*Dimension including the plating thickness
Base material dimension

Hitachi Code	TTP-20DA
JEDEC	—
EIAJ	—
Weight (reference value)	0.07 g

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